

# Phase Control Thyristors (Hockey PUK Version), 560 A



**B-PUK (TO-200AC)** 

PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	560 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	400 V, 800 V, 1200 V, 1600 V, 1800 V, 2000 V				
V <sub>TM</sub>	2.18 V				
I <sub>GT</sub>	100 mA				
$T_J$	-40 °C to +125 °C				
Package	B-PUK (TO-200AC)				
Circuit configuration	Single SCR				

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)



- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	R TEST CONDITIONS VALUES		UNITS			
1		560	Α			
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C			
1		1115	Α			
IT(RMS)	T <sub>hs</sub>	25	°C			
1	50 Hz	8000	А			
ITSM	60 Hz	8380	A			
l <sup>2</sup> t	50 Hz	320	kA <sup>2</sup> s			
I-1	60 Hz	292	KA-5			
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 2000	V			
tq	Typical	100	μs			
T <sub>J</sub>		-40 to 125	°C			

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA				
	04	400	500					
	08	800	900					
VS-ST300CL		1200	1300	50				
VO 010000L	16	1600	1700	30				
18 1800 20 2000		1800	1900					
		2000	2100					



ABSOLUTE MAXIMUM RATINGS						•
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Maximum average on-state current	1	180° condu	ction, half sine v	vave	560 (275)	Α
at heatsink temperature	I <sub>T(AV)</sub>	double side	(single side) co	oled	55 (75)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	1115	
		t = 10 ms	No voltage		8000	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		8380	A kA <sup>2</sup> s
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		6730	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	7040	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	reapplied	initial $T_J = T_J$ maximum	320	
	l <sup>2</sup> t	t = 8.3 ms			292	
		t = 10 ms			226	
		t = 8.3 ms	reapplied		207	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10	t = 0.1 to 10 ms, no voltage reapplied			kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.97	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			V
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			0.74	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.73	1115.2
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 1635 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			2.18	٧
Maximum holding current	I <sub>H</sub>	T 05 00	T 05:00 I 10V IV I			m 1
Typical latching current	ΙL	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load			1000	mA

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dI/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs		
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0			
Typical turn-off time	t <sub>q</sub>	$I_{TM}$ = 550 A, $T_J$ = $T_J$ maximum, dl/dt = 40 A/μs, $V_R$ = 50 V, dV/dt = 20 V/μs, gate 0 V 100 $\Omega$ , $t_p$ = 500 μs	100	μs		

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub>	500	V/µs		
Maximum peak reverse and off-state leakage current	I <sub>RRM,</sub> I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	50	mA		



TRIGGERING							
DADAMETED	CVMDOL	TEST SOURITIONS		VALUES		што	
PARAMETER	ARAMETER SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS		
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10	0.0	w	
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	VV	
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	3	.0	Α	
Maximum peak positive gate voltage	+ V <sub>GM</sub>	T T 12 1 15		GM		20	V
Maximum peak negative gate voltage	- V <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le 5$ ms			.0	V	
		T <sub>J</sub> = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest	200	-		
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C		100	200	mA	
		T <sub>J</sub> = 125 °C		50	-		
		$T_J = -40  ^{\circ}C$	value which will trigger all units	2.5	-		
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.8	3.0	V	
		T <sub>J</sub> = 125 °C		1.1	-		
DC gate current not to trigger	$I_{GD}$		Maximum gate current/	10	0.0	mA	
DC gate voltage not to trigger	$V_{\mathrm{GD}}$	$T_J = T_J$ maximum	voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRN</sub> anode to cathode applied		0.25		

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	$T_J$		-40 to 125	- °C		
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150			
Maximum thermal resistance, junction to heatsink	В	DC operation single side cooled	0.11			
maximum thermal resistance, junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.05	K/W		
Maximum thormal registance, ages to be striple	R <sub>thC-hs</sub>	DC operation single side cooled	0.011	IVVV		
Maximum thermal resistance, case to heatsink		DC operation double side cooled	0.006			
Mounting force, ± 10 %			9800	N		
Woulding force, ± 10 %			(1000)	(kg)		
Approximate weight			250	g		
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-2	200AC)		

△R <sub>thJ-hs</sub> CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS	
180°	0.012	0.010	0.008	0.008	$T_J = T_J$ maximum	K/W	
120°	0.014	0.015	0.014	0.014			
90°	0.018	0.018	0.019	0.019			
60°	0.026	0.027	0.027	0.028			
30°	0.045	0.046	0.046	0.046			

#### Note

• The table above shows the increment of thermal resistance RthJ-hs when devices operate at different conduction angles than DC

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# Vishay Semiconductors

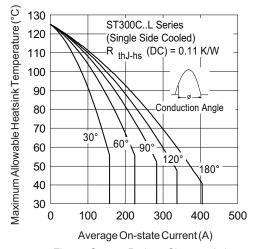


Fig. 1 - Current Ratings Characteristics

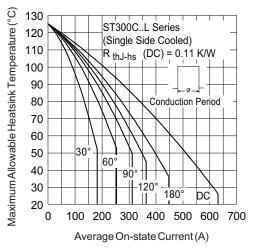


Fig. 2 - Current Ratings Characteristics

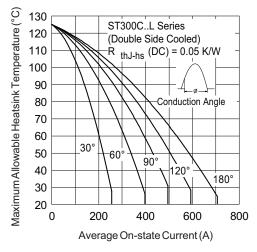


Fig. 3 - Current Ratings Characteristics

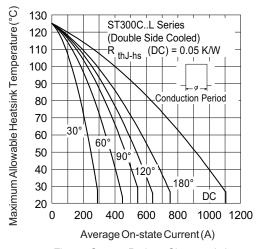


Fig. 4 - Current Ratings Characteristics

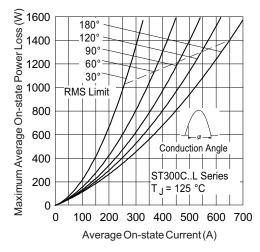


Fig. 5 - On-State Power Loss Characteristics

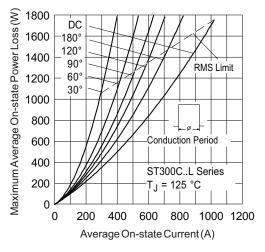


Fig. 6 - On-State Power Loss Characteristics

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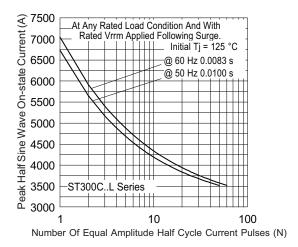


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

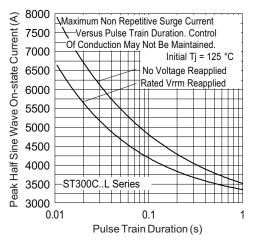


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

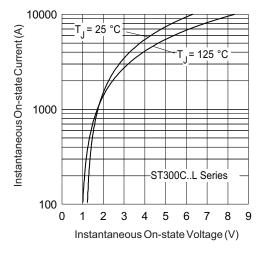


Fig. 9 - On-State Voltage Drop Characteristcs

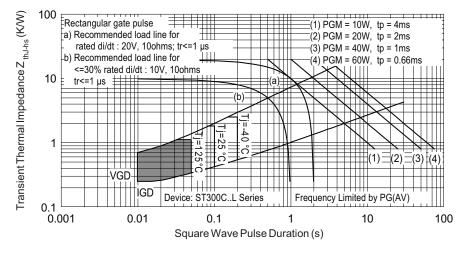


Fig. 1 - Thermal Impedance Z<sub>thJ-hs</sub> Characteristics

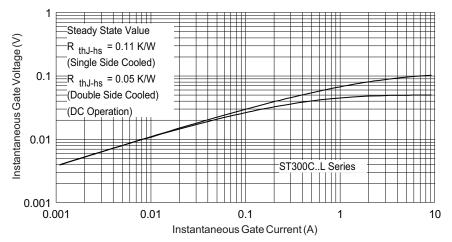
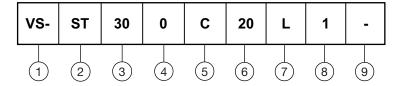


Fig. 10 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**





1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

6 - Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

7 - L = PUK case B-PUK (TO-200AC)

**8** - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

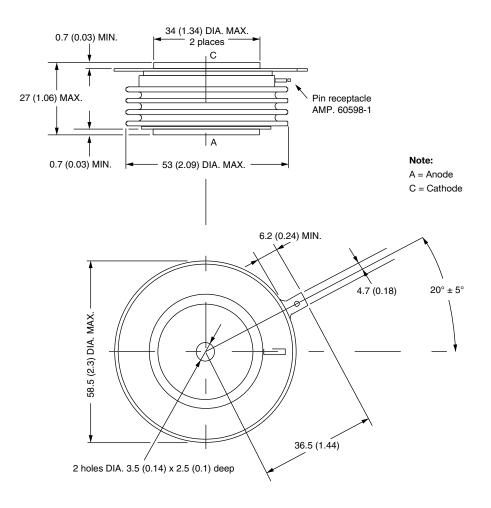
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95076		



# **B-PUK (TO-200AC)**

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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